Notice of References Cited

Application/Control No. 10/059,176	Applicant(s)/Patent Under Reexamination HAYASHI, HIROKAZU			
Examiner	Art Unit			
Akash Saxena	2128	Page 1 of 2		

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	Α	US-6,154,717	11-2000	Kumashiro, Shigetaka	703/2
	В	US-5,930,494	07-1999	Akiyama, Yutaka	703/7
	С	US-6,080,200	06-2000	Kumashiro, Shigetaka	703/13
	D	US-6,006,026	12-1999	Kumashiro, Shigetaka	703/2
	E	US-6,327,555	12-2001	Shimizu et al.	703/12
	F	US-6,154,718	11-2000	Sakamoto, Hironori	703/12
	G	US-6,006,026	12-1999	Kumashiro, Shigetaka	703/2
	Н	US-6,148,276	11-2000	Sakamoto, Hironori	703/13
	1	US-6,144,929	11-2000	Kumashiro, Shigetaka	703/2
	J	US-6,120,548	09-2000	Jarvis et al.	703/2
	к	US-6,041,174	03-2000	Akiyama, Yutaka	703/12
	L	US-5,999,719	12-1999	Asada et al.	703/12
	М	US-5,557,710	09-1996	Amdursky et al.	345/419

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N	·				
	0					
	Р					
	Q					
	R					
	s					
	T					

NON-PATENT DOCUMENTS

* Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)				
	U	"Physics-Based Threshold Voltage Modeling with Reverse Short Channel Effect"; K-Y Lim et al; 1999 Journal of Modeling and Simulation of Microsystems, Vol 2, No. 1, Pages 51-56		
	v	"The improvement of short-channel effects due to oxidation-induced boron redistribution for counter-implantation p-MOSFET's"; Perng, RK. et al; Electron Device Letters, IEEE Volume 14, Issue 5, May 1993 Page(s):237 - 239		
	w	"A highly efficient adaptive mesh approach to semiconductor device simulation-application to impact ionization analysis"; Dang, R. et al; Magnetics, IEEE Transactions on Volume 27, Issue 5, Sep 1991 Page(s):4162 - 4165 □□		
	х	New models for the simulation of polysilicon impurity diffusion sources for a wide range of process conditions"; Kamohara, S. et al; Bipolar/BiCMOS Circuits and Technology Meeting, 1992., Proceedings of the 1992 7-8 Oct. 1 Page(s):126 - 129		

^{*}A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)

Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.

Notice of References Cited Application/Control No. 10/059,176 Examiner Akash Saxena Applicant(s)/Patent Under Reexamination HAYASHI, HIROKAZU Page 2 of 2

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	Α	US-6,505,147	01-2003	Kumashiro, Shigetaka	703/2
	В	US-5,889,687	03-1999	Enda, Toshiyuki	703/4
	С	US-4,607,530	08-1986	Chow, Edward Y.	702/98
	D	US-6,594,625	07-2003	Hayashi, Hirokazu	703/2
	Е	US-6,684,181	01-2004	Sawahata, Koichi	703/2
	F	US-6,285,970	09-2001	Akiyama, Yutaka	703/2
	G	US-6,581,028	06-2003	Hayashi, Hirokazu	703/2
-	Н	US-6,242,272	06-2001	Kumashiro et al.	438/14
	_	US-			
	J	US-			
	К	US-			
	L	US-			
	М	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	0					
	Р					
	œ					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)					
	U	"Mathworld: Solid Angle"; 1999; http://mathworld.wolfram.com/SolidAngle.html					
	٧						
	w						
	x						

^{*}A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)

Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.